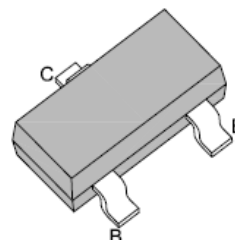


## SMD General Purpose Transistor (PNP)

### Features

- PNP Silicon Epitaxial Planar Transistor for Switching and Amplifier Applications



### Mechanical Data

<b>Case:</b>	SOT-23, Plastic Package
<b>Terminals:</b>	Solderable per MIL-STD-202G, Method 208
<b>Weight:</b>	0.008 gram

SOT-23



### Marking Information

	BC856A	BC856B	BC857A	BC857B	BC857C	BC858A	BC858B	BC858C
Marking Code	3A	3B	3E	3F	3G	3J	3K	3L

### Maximum Ratings ( $T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	BC856	BC857	BC858	Unit	Conditions
<b>-V<sub>CB0</sub></b>	Collector-Base Voltage	80	50	30	V	
<b>-V<sub>CEO</sub></b>	Collector-Emitter Voltage	65	45	30	V	
<b>-V<sub>EB0</sub></b>	Emitter-Base Voltage	5	5	5	V	
<b>-I<sub>c</sub></b>	Collector Current	100			mA	
<b>P<sub>tot</sub></b>	Power Dissipation	350			mW	Note 1
<b>T<sub>J</sub></b>	Junction Temperature	150			°C	
<b>T<sub>STG</sub></b>	Storage Temperature Range	-55 to +150			°C	

**Note:** 1. Package mounted on 99.5% Alumina 10 x 8 x 0.6mm.

# SMD General Purpose Transistor (PNP)

## BC856/BC857/BC858

### Electrical Characteristics ( $T_{Ambient}=25^{\circ}C$ unless noted otherwise)

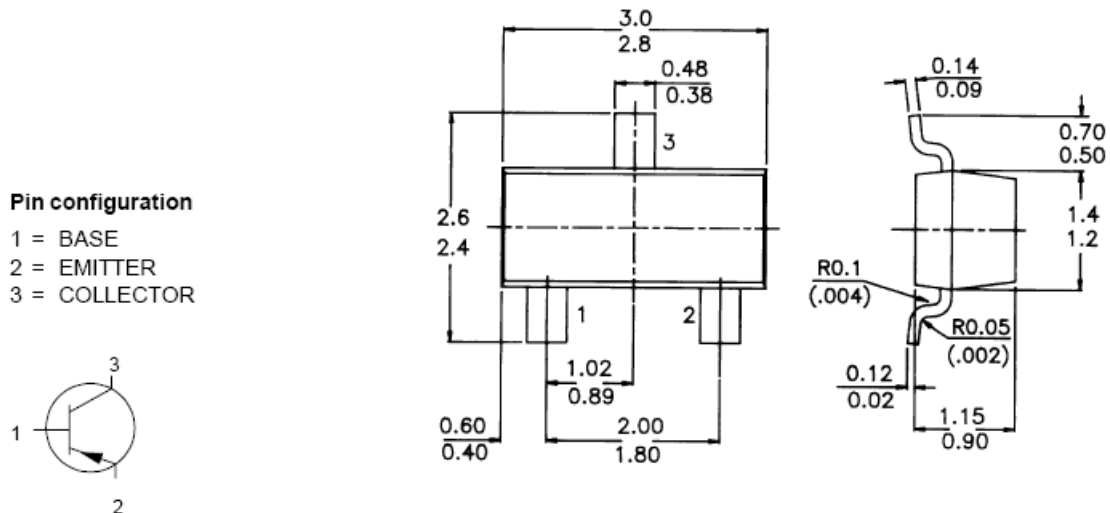
Symbol	Description		Min.	Typ.	Max.	Unit	Conditions
<b>-I<sub>CBO</sub></b>	Collector-Emitter Cut-off Current		-	-	15	nA	-V <sub>CB</sub> =30V, I <sub>E</sub> =0
<b>h<sub>FE</sub></b>	D.C. Current Gain	BC856/7/8, Suffix 'A'	-	90	-		-V <sub>CE</sub> =5V, -I <sub>C</sub> =10μA
		BC856/7/8, Suffix 'B'	-	150	-		
		BC857/8, Suffix 'C'	-	270	-		
		BC856/7/8, Suffix 'A'	110	180	220		-V <sub>CE</sub> =5V, -I <sub>C</sub> =2mA
		BC856/7/8, Suffix 'B'	200	290	450		
		BC857/8, Suffix 'C'	420	520	800		
<b>-V<sub>CE(sat)</sub></b>	Collector-Emitter Saturation Voltage		-	0.09	0.3	V	-I <sub>C</sub> =10mA, -I <sub>B</sub> =0.5mA
			-	0.25	0.65		-I <sub>C</sub> =100mA, -I <sub>B</sub> =5mA
<b>-V<sub>BE(sat)</sub></b>	Base-Emitter Saturation Voltage		-	0.7	-	V	-I <sub>C</sub> =10mA, -I <sub>B</sub> =0.5mA
			-	0.9	-		-I <sub>C</sub> =100mA, -I <sub>B</sub> =5mA
<b>-V<sub>BE(on)</sub></b>	Base-Emitter On Voltage		0.6	0.65	0.75	V	-V <sub>CE</sub> =5V, -I <sub>C</sub> =2mA
			-	-	0.82		-V <sub>CE</sub> =5V, -I <sub>C</sub> =10mA
<b>f<sub>T</sub></b>	Current Gain-Bandwidth Product		-	150	-	MHz	-V <sub>CE</sub> =5V, -I <sub>C</sub> =10mA, f=100MHz
<b>C<sub>ob</sub></b>	Collector Output Capacitance		-	4.5	-	pF	-V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz
<b>NF</b>	Noise Figure		-	2.0	10	dB	-V <sub>CE</sub> =5V, -I <sub>C</sub> =0.2mA, R <sub>G</sub> =2KΩ, f=1KHz

# SMD General Purpose Transistor (PNP)

## BC856/BC857/BC858

Dimensions in mm

### SOT-23



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